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**Question Paper Code : 52440**

**B.E./B.Tech. DEGREE EXAMINATION, NOVEMBER/DECEMBER 2017**

**Third Semester**

**Electronics and Communication Engineering**

**EC 2205 – ELECTRONIC CIRCUITS – I**

**[Common to Medical Electronics Engineering]**

**(Regulations 2008)**

**Time : Three Hours**

**Maximum : 100 Marks**

**Answer ALL questions**

**PART – A**

**(10×2=20 Marks)**

1. What is the advantage of having an emitter resistor in BJT biasing circuit ?
2. What is the impact of temperature on drain current of MOSFET ?
3. Draw the small-signal ac equivalent circuit of the BJT.
4. Define CMRR.
5. Draw the high frequency small-signal equivalent circuit of a MOSFET.
6. Determine the unity-gain bandwidth of a FET with parameters,  $C_{gd} = 10 \text{ fF}$ ,  $C_{gs} = 50 \text{ fF}$  and  $g_m = 1.2 \text{ mA/V}$ .
7. What is thermal runaway ?
8. What is second harmonic distortion ?
9. Give the expressions for ripple factor of a full wave rectifier without and with capacitive filter.
10. What is advantage of SMPS over linear power supply ?



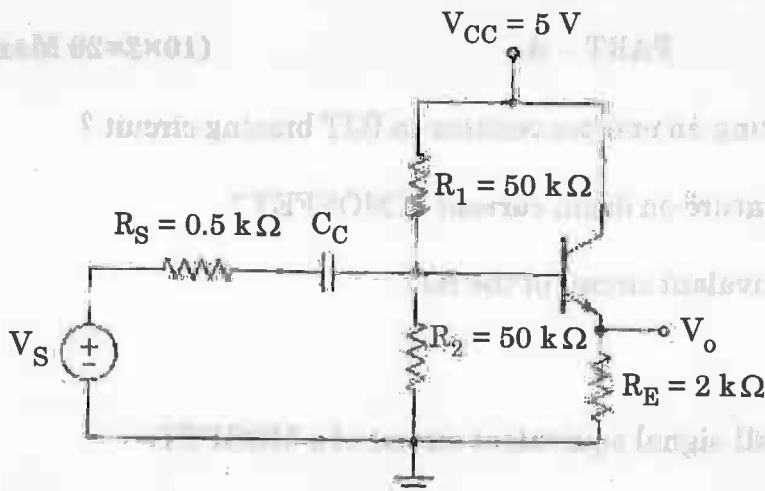
## PART - B

(5×16=80 Marks)

11. a) Analyze a BJT with a voltage divider bias circuit, and determine the change in the Q-point with a variation in  $\beta$  when the circuit contains an emitter resistor. Let the biasing resistors be  $R_{B1} = 56 \text{ k}\Omega$ ,  $R_{B2} = 12.2 \text{ k}\Omega$ ,  $R_C = 2 \text{ k}\Omega$ ,  $R_E = 0.4 \text{ k}\Omega$ ,  $V_{CC} = 10 \text{ V}$ ,  $V_{BE(\text{on})} = 0.7 \text{ V}$  and  $\beta = 100$ .

(OR)

- b) Discuss on bias stabilization using self-bias. Also derive the expressions for the different stability factors for a self-biased BJT circuit.
12. a) Derive the expression for small-signal voltage gain of the emitter-follower circuit shown in the figure below. Also calculate the small-signal voltage gain assuming the transistor parameters as  $\beta = 100$ ,  $V_{BE(\text{on})} = 0.7 \text{ V}$  and  $V_A = 80 \text{ V}$ .



(OR)

- b) Analyze a basic common-base amplifier circuit and derive the expressions for its small-signal voltage gain, current gain, input impedance and output impedance.
13. a) Derive the expression for cut-off frequency of a BJT. Also determine the 3 dB bandwidth and cut-off frequency of the BJT biased at  $I_C = 0.15 \text{ mA}$  and has parameters  $\beta_0 = 150$ ,  $C_\pi = 0.8 \text{ pF}$  and  $C_\mu = 0.012 \text{ pF}$ .

(OR)

- b) Derive the expression for Miller capacitance in BJT and draw the equivalent circuit of a common-emitter amplifier including the Miller capacitance. Also determine the 3 dB frequency of the current gain for the circuit both with and without the effect of  $C_M$  for the given circuit parameters :  $R_C = R_L = 4 \text{ k}\Omega$ ,  $r_\pi = 2.6 \text{ k}\Omega$ ,  $R_B = 200 \text{ k}\Omega$ ,  $C_\pi = 0.8 \text{ pF}$ ,  $C_\mu = 0.05 \text{ pF}$  and  $g_m = 38.5 \text{ mA/V}$ .
14. a) With neat diagrams, explain the operation of the following power amplifiers and derive the expression for their maximum theoretical efficiency.
- i) Transformer-coupled Class-A amplifier.
  - ii) Class-B push-pull amplifier.
- (OR)
- b) With neat diagrams, explain the operation of Class-C, Class-D and Class-S power amplifiers. Also list the advantages, disadvantages and applications.
15. a) With necessary diagrams, explain the operation of half-wave and full-wave rectifiers. Also derive and compare their ripple factor values.
- (OR)
- b) Explain the operation of a simple zener voltage regulator. Also explain how overload protection can be implemented through current-limiting circuit.

1. The circuit shown in Figure 1 is a common-emitter amplifier. The input signal is  $v_i(t) = 0.1 \cos(2000\pi t)$  V. The load resistor is  $R_L = 10 \text{ k}\Omega$ . The transistor has  $\beta = 100$  and  $V_{BE} = 0.7$  V. The circuit parameters are  $R_1 = 10 \text{ k}\Omega$ ,  $R_2 = 10 \text{ k}\Omega$ ,  $R_E = 1 \text{ k}\Omega$ ,  $R_C = 10 \text{ k}\Omega$ , and  $V_{CC} = 10$  V. Calculate the average power delivered to the load resistor.

2. The circuit shown in Figure 2 is a common-emitter amplifier. The input signal is  $v_i(t) = 0.1 \cos(2000\pi t)$  V. The load resistor is  $R_L = 10 \text{ k}\Omega$ . The transistor has  $\beta = 100$  and  $V_{BE} = 0.7$  V. The circuit parameters are  $R_1 = 10 \text{ k}\Omega$ ,  $R_2 = 10 \text{ k}\Omega$ ,  $R_E = 1 \text{ k}\Omega$ ,  $R_C = 10 \text{ k}\Omega$ , and  $V_{CC} = 10$  V. Calculate the average power delivered to the load resistor.

3. The circuit shown in Figure 3 is a common-emitter amplifier. The input signal is  $v_i(t) = 0.1 \cos(2000\pi t)$  V. The load resistor is  $R_L = 10 \text{ k}\Omega$ . The transistor has  $\beta = 100$  and  $V_{BE} = 0.7$  V. The circuit parameters are  $R_1 = 10 \text{ k}\Omega$ ,  $R_2 = 10 \text{ k}\Omega$ ,  $R_E = 1 \text{ k}\Omega$ ,  $R_C = 10 \text{ k}\Omega$ , and  $V_{CC} = 10$  V. Calculate the average power delivered to the load resistor.

4. The circuit shown in Figure 4 is a common-emitter amplifier. The input signal is  $v_i(t) = 0.1 \cos(2000\pi t)$  V. The load resistor is  $R_L = 10 \text{ k}\Omega$ . The transistor has  $\beta = 100$  and  $V_{BE} = 0.7$  V. The circuit parameters are  $R_1 = 10 \text{ k}\Omega$ ,  $R_2 = 10 \text{ k}\Omega$ ,  $R_E = 1 \text{ k}\Omega$ ,  $R_C = 10 \text{ k}\Omega$ , and  $V_{CC} = 10$  V. Calculate the average power delivered to the load resistor.